

	Hit s	Search Text	DBs
2	34	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4) same trim\$4)	US-PPGUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	30	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4) near36 (pattern\$4 or (elevated near9 structure))) and trim\$4	US-PPGUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
4	36	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4)) and (trim\$4 near9 (mask or reticle or photomask))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
5	40	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4)) and trim\$4 and (first near9 (mask or pattern)) and (second near12 (mask or pattern))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
6	46	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4)) and (trim\$4)	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
7	149	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4)) and (first near16 (resist or photoresist) near12 (mask or pattern)) and (second near12 (resist or photoresist) near9 (mask or pattern)) and (second near12 develop\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
8	37	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4)) and (first near16 (resist or photoresist) near12 (mask or pattern)) and (second near12 (resist or photoresist) near9 (mask or pattern)) and (trim\$5)	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
9	37	<p>((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4)) and (first near16 (resist or photoresist) near12 (mask or pattern)) and (second near12 (resist or photoresist) near9 (mask or pattern)) and (second near12 develop\$4 near16 (trim\$4 or etch\$4))</p>	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
10	46	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4)) and (trim\$4)	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
11	149	((wafer or substrate or workpiece) same ((insulator or dielectric or metal\$4 or conductive) near9 (layer or deposit\$4 or film\$3 or form\$3 or coat\$4)) same (resist or photoresist or photosensitive) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((mask or photomask or reticle) same ((phase near4 shift\$4) or (alternat\$4 near9 phase) or attenuat\$4)) and ((second or third) near6 (mask or reticle or photomask)) and ((second or third) near12 (photoresist or resist or photosensitive) near16 (layer or film or coat\$4 or deposit\$4 or form\$4)) and (first near16 (resist or photoresist) near12 (mask or pattern)) and (second near12 (resist or photoresist) near9 (mask or pattern)) and (second near12 develop\$4)	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
12	126	S11 NOT S10	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
13	5	S12 and ((trim\$4 or reduc\$4) near22 (linewidth or width) near26 (pattern or mask) near22 (resist or photoresist or photosensitive))	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

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14	25	S12 and ((trim\$4 or reduc\$4) near22 (linewidth or width))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM TDB
15	49	S15 and S16	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM TDB
16	486	((deposit\$4 or coat\$4 or form\$4 or apply\$4) near22 (conductive or metal\$4 or insulat\$4 or dielectric or Ni or Cu)) same (second near8 (photoresist or resist or photosensitive) near12 (layer or form\$3 or film or deposit\$4 or coat\$4) near22 (expos\$4 or irradiat\$4 or illuminat\$4) near36 (trim\$4 or (reduc\$5 near9 (size or width)) or etch\$4) near26 develop\$4))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM TDB
17	170	((first near5 (photoresist or resist or photosensitive) near9 (layer or material or coat\$3 or deposit\$3 or film or form\$3) near22 (expos\$4 or illuminat\$4 or irradiat\$4) near35 (mask or reticle or photomask or phase\$4shift\$4mask or (alternat\$5 near6 shift\$5 near8 (\$4mask or reticle))) near29 develop\$4) same (strip\$4 or remov\$4 or wash\$4) same (((hard near5 mask) or metal\$4 or conductive or insulat\$4 or dielectric) near9 pattern))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM TDB